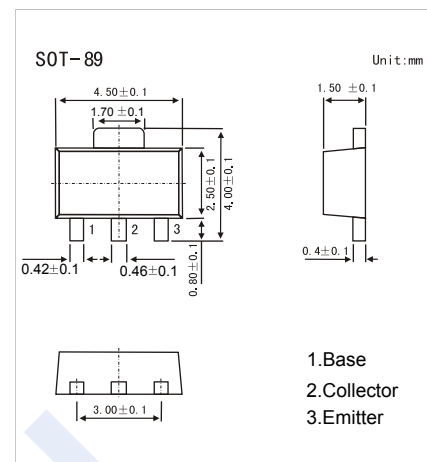


NPN Transistors

2SC3736

■ Features

- High Speed, High Voltage Switching
- Low Collector Saturation Voltage
- Complementary to 2SA1463



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	80	V
Collector - Emitter Voltage	V _{CE0}	45	
Emitter - Base Voltage	V _{EB0}	5	
Collector Current - Continuous	I _C	1	A
Collector Current - Pulse *1	I _{CP}	2	
Collector Power Dissipation	P _C	2	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

*1 : Pulse :PW ≤ 10ms, Duty Cycle ≤ 50%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E = 0	80			V
Collector-emitter breakdown voltage	V _{CE0}	I _C = 1 mA, I _B = 0	45			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C = 0	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 80V, I _E = 0			0.5	μA
Emitter cut-off current	I _{EB0}	V _{EB} = 4V, I _C = 0			0.5	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500 mA, I _B =50mA		0.17	0.4	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =500 mA, I _B =50mA		0.9	1.2	
DC current gain	h _{FE}	V _{CE} = 10V, I _C = 50mA	60		200	
Turn-on time	t _{on}	I _C =500mA, I _{B1} =-I _{B2} =50mA		20	40	ns
Storage time	t _{stg}			55	80	
Turn-off time	t _{off}			72	100	
Collector output capacitance	C _{ob}	V _{CB} = 5V, I _E = 0, f=1MHz		6.7	10	pF
Transition frequency	f _T	V _{CE} = 10V, I _E = -100mA	300	380		MHz

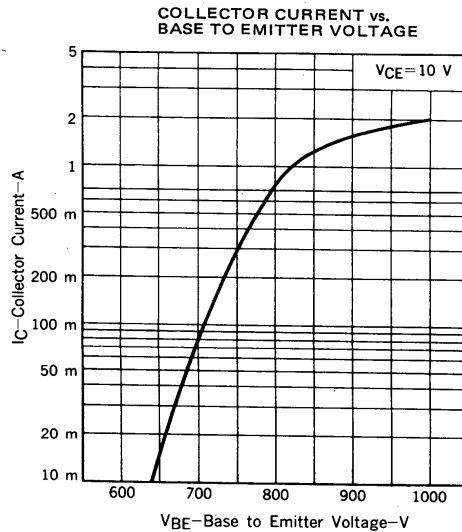
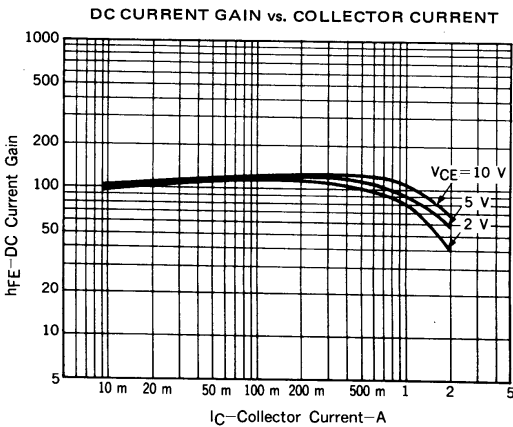
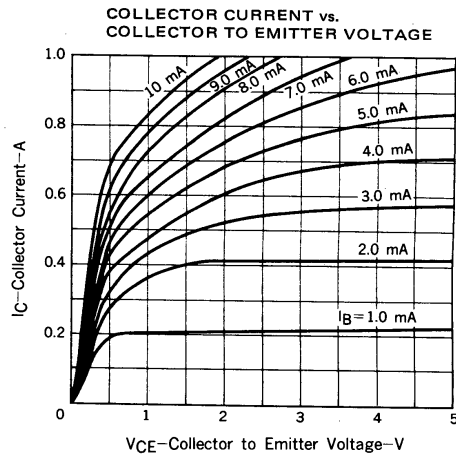
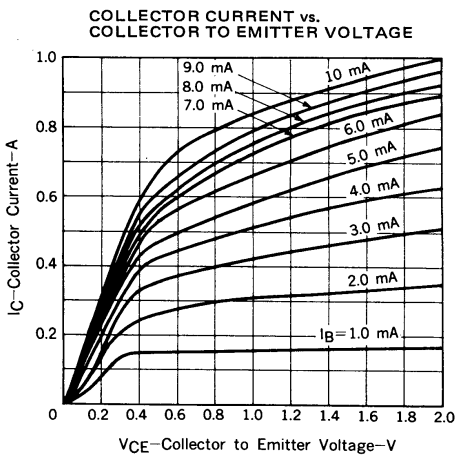
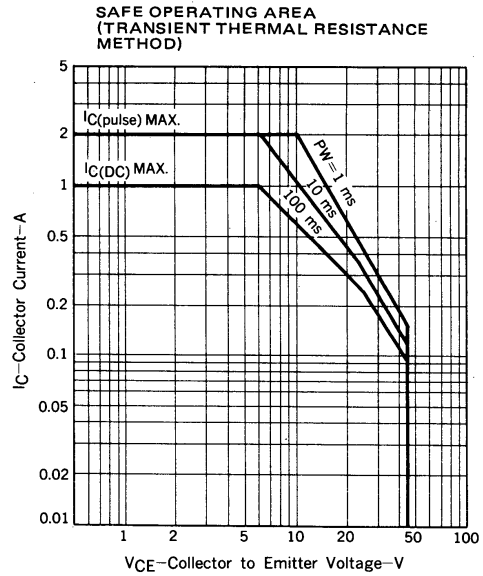
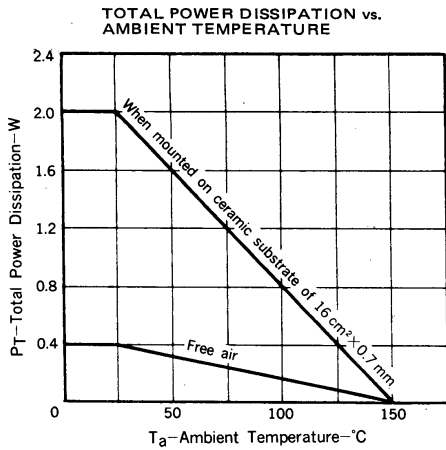
■ Classification of h_{FE}

Type	2SC3736-L	2SC3736-K
Range	60-120	100-200
Marking	OL	OK

NPN Transistors

2SC3736

Typical Characteristics



NPN Transistors

2SC3736

■ Typical Characteristics

